

# 2SK3048

## Silicon N-Channel Power F-MOS FET

### ■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

### ■ Applications

- Contactless relay
- Driving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

### ■ Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

| Parameter                         | Symbol                   | Ratings     | Unit             |
|-----------------------------------|--------------------------|-------------|------------------|
| Drain to Source breakdown voltage | $V_{DSS}$                | 600         | V                |
| Gate to Source voltage            | $V_{GSS}$                | $\pm 30$    | V                |
| Drain current                     | DC                       | $I_D$       | A                |
|                                   | Pulse                    | $I_{DP}$    | A                |
| Avalanche energy capacity         | EAS*                     | 22.5        | mJ               |
| Allowable power dissipation       | $T_C = 25^\circ\text{C}$ | $P_D$       | W                |
|                                   | $T_a = 25^\circ\text{C}$ | 2           |                  |
| Channel temperature               | $T_{ch}$                 | 150         | $^\circ\text{C}$ |
| Storage temperature               | $T_{stg}$                | -55 to +150 | $^\circ\text{C}$ |

\*  $L = 5\text{mH}$ ,  $I_L = 3\text{A}$ , 1 pulse

### ■ Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

| Parameter                                    | Symbol       | Conditions  | min | typ | max     | Unit          |
|--|--------------|---|-----|-----|---------|---------------|
| Drain to Source cut-off current              | $I_{DSS}$    | $V_{DS} = 480\text{V}$ , $V_{GS} = 0$   |     |     | 100     | $\mu\text{A}$ |
| Gate to Source leakage current               | $I_{GSS}$    | $V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0$  |     |     | $\pm 1$ | $\mu\text{A}$ |
| Drain to Source breakdown voltage            | $V_{DSS}$    | $I_D = 1\text{mA}$ , $V_{GS} = 0$   | 600 |     |         | V             |
| Gate threshold voltage                       | $V_{th}$     | $V_{DS} = 25\text{V}$ , $I_D = 1\text{mA}$  | 2   |     | 5       | V             |
| Drain to Source ON-resistance                | $R_{DS(on)}$ | $V_{GS} = 10\text{V}$ , $I_D = 2\text{A}$   |     | 1.7 | 2.5     | $\Omega$      |
| Forward transfer admittance                  | $ Y_{fs} $   | $V_{DS} = 25\text{V}$ , $I_D = 2\text{A}$   | 1.5 | 2.5 |         | S             |
| Diode forward voltage                        | $V_{DSF}$    | $I_{DR} = 3\text{A}$ , $V_{GS} = 0$   |     |     | -1.5    | V             |
| Input capacitance (Common Source)            | $C_{iss}$    |   |     | 750 |         | pF            |
| Output capacitance (Common Source)           | $C_{oss}$    | $V_{DS} = 20\text{V}$ , $V_{GS} = 0$ , $f = 1\text{MHz}$                                |     | 80  |         | pF            |
| Reverse transfer capacitance (Common Source) | $C_{rss}$    |   |     | 25  |         | pF            |
| Turn-on time (delay time)                    | $t_{d(on)}$  |   |     | 15  |         | ns            |
| Rise time                                    | $t_r$        | $V_{DD} = 200\text{V}$ , $I_D = 2\text{A}$<br>$V_{GS} = 10\text{V}$ , $R_L = 100\Omega$ |     | 25  |         | ns            |
| Turn-off time (delay time)                   | $t_{d(off)}$ |   |     | 90  |         | ns            |
| Fall time                                    | $t_f$        |   |     | 40  |         | ns            |





